

**Features**

- Pin-and function-compatible with CY7C1011CV33
- High speed
  - $t_{AA} = 10 \text{ ns}$
- Low active power
  - $I_{CC} = 90 \text{ mA @ } 10 \text{ ns (Industrial)}$
- Low CMOS standby power
  - $I_{SB2} = 10 \text{ mA}$
- Data Retention at 2.0 V
- Automatic power-down when deselected
- Independent control of upper and lower bits
- Easy memory expansion with  $\overline{CE}$  and  $\overline{OE}$  features
- Available in Pb-free 44-pin TSOP II, and 48-ball VFBGA

**Functional Description**

The CY7C1011DV33<sup>[1]</sup> is a high-performance CMOS Static RAM organized as 128 K words by 16 bits.

Writing to the device is accomplished by taking Chip Enable ( $\overline{CE}$ ) and Write Enable ( $\overline{WE}$ ) inputs LOW. If Byte Low Enable ( $\overline{BLE}$ ) is LOW, then data from I/O pins (I/O<sub>0</sub> through I/O<sub>7</sub>), is written into the location specified on the address pins (A<sub>0</sub> through A<sub>16</sub>). If Byte High Enable ( $\overline{BHE}$ ) is LOW, then data from I/O pins (I/O<sub>8</sub> through I/O<sub>15</sub>) is written into the location specified on the address pins (A<sub>0</sub> through A<sub>16</sub>).

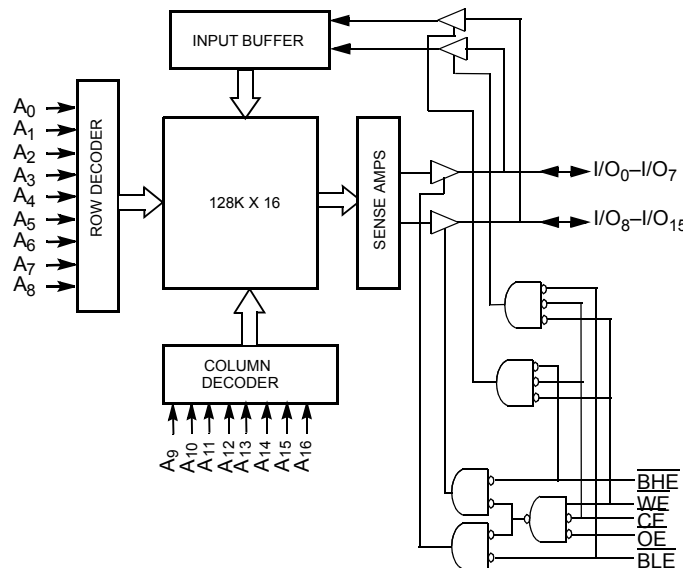
Reading from the device is accomplished by taking Chip Enable ( $\overline{CE}$ ) and Output Enable ( $\overline{OE}$ ) LOW while forcing the Write Enable ( $\overline{WE}$ ) HIGH. If Byte Low Enable ( $\overline{BLE}$ ) is LOW, then data from the memory location specified by the address pins will appear on I/O<sub>0</sub> to I/O<sub>7</sub>. If Byte High Enable ( $\overline{BHE}$ ) is LOW, then data from memory will appear on I/O<sub>8</sub> to I/O<sub>15</sub>. See the truth table at the back of this data sheet for a complete description of read and write modes.

The input/output pins (I/O<sub>0</sub> through I/O<sub>15</sub>) are placed in a high-impedance state when the device is deselected ( $\overline{CE}$  HIGH), the outputs are disabled ( $\overline{OE}$  HIGH), the  $\overline{BHE}$  and  $\overline{BLE}$  are disabled ( $\overline{BHE}$ ,  $\overline{BLE}$  HIGH), or during a write operation ( $\overline{CE}$  LOW, and  $\overline{WE}$  LOW).

The CY7C1011DV33 is available in standard Pb-free 44-pin TSOP II with center power and ground pinout, as well as 48-ball very fine-pitch ball grid array (VFBGA) packages.

For a complete list of related resources, [click here](#).

**Logic Block Diagram**



**Note**

1. For guidelines on SRAM system design, please refer to the "System Design Guidelines" Cypress application note, available on the internet at [www.cypress.com](http://www.cypress.com)

## Contents

<b>Selection Guide</b> .....	<b>3</b>	<b>Ordering Information</b> .....	<b>12</b>
<b>Pin Configurations</b> .....	<b>3</b>	Ordering Code Definitions .....	12
<b>Maximum Ratings</b> .....	<b>4</b>	<b>Package Diagrams</b> .....	<b>13</b>
<b>Operating Range</b> .....	<b>4</b>	<b>Acronyms</b> .....	<b>14</b>
<b>DC Electrical Characteristics</b> .....	<b>4</b>	<b>Document Conventions</b> .....	<b>14</b>
<b>Capacitance</b> .....	<b>5</b>	Units of Measure .....	14
<b>Thermal Resistance</b> .....	<b>5</b>	<b>Document History</b> .....	<b>15</b>
<b>AC Test Loads and Waveforms</b> .....	<b>5</b>	<b>Sales, Solutions, and Legal Information</b> .....	<b>17</b>
<b>Data Retention Characteristics</b> .....	<b>6</b>	Worldwide Sales and Design Support .....	17
<b>Data Retention Waveform</b> .....	<b>6</b>	Products .....	17
<b>AC Switching Characteristics</b> .....	<b>7</b>	PSoC® Solutions .....	17
<b>Switching Waveforms</b> .....	<b>8</b>	Cypress Developer Community .....	17
<b>Truth Table</b> .....	<b>11</b>	Technical Support .....	17

### Selection Guide

Description	-10	Unit
Maximum Access Time	10	ns
Maximum Operating Current	90	mA
Maximum CMOS Standby Current	10	mA

### Pin Configurations

Figure 1. 44-pin TSOP II pinout (Top View)

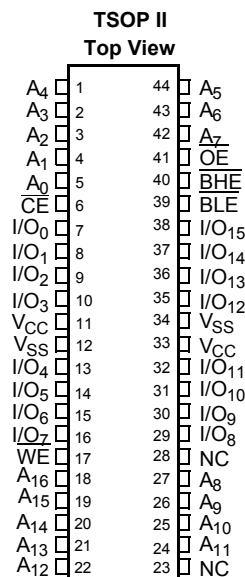
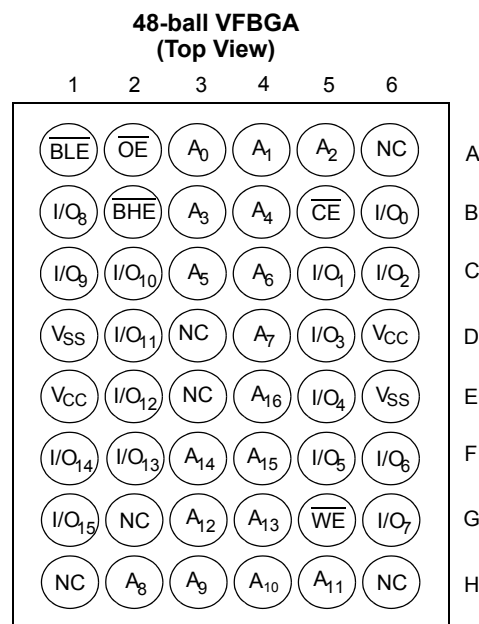


Figure 2. 48-ball VFBGA pinout (Top View)



## Maximum Ratings

Exceeding maximum ratings may shorten the useful life of the device. User guidelines are not tested.

Storage temperature ..... -65 °C to +150 °C

Ambient temperature with power applied ..... -55 °C to +125 °C

Supply voltage on  $V_{CC}$  to relative GND <sup>[2]</sup> ..... -0.3 V to +4.6 V

DC voltage applied to outputs in high Z State <sup>[2]</sup> ..... -0.3 V to  $V_{CC} + 0.3$  V

DC input voltage <sup>[2]</sup> ..... -0.3 V to  $V_{CC} + 0.3$  V

Current into outputs (LOW) ..... 20 mA

Static discharge voltage (per MIL-STD-883, method 3015) ..... > 2001 V

Latch-up current ..... > 200 mA

## Operating Range

Range	Ambient Temperature	$V_{CC}$
Industrial	-40 °C to +85 °C	3.3 V ± 0.3 V

## DC Electrical Characteristics

Over the Operating Range

Parameter	Description	Test Conditions	-10		Unit	
			Min	Max		
$V_{OH}$	Output HIGH voltage	$V_{CC} = \text{Min}, I_{OH} = -4.0 \text{ mA}$	2.4	-	V	
$V_{OL}$	Output LOW voltage	$V_{CC} = \text{Min}, I_{OL} = 8.0 \text{ mA}$	-	0.4	V	
$V_{IH}$	Input HIGH voltage		2.0	$V_{CC} + 0.3$	V	
$V_{IL}$	Input LOW voltage <sup>[3]</sup>		-0.3	0.8	V	
$I_{IX}$	Input leakage current	$GND \leq V_I \leq V_{CC}$	-1	+1	μA	
$I_{OZ}$	Output leakage current	$GND \leq V_{OUT} \leq V_{CC}$ , Output Disabled	-1	+1	μA	
$I_{CC}$	$V_{CC}$ operating supply current	$V_{CC} = \text{Max}, f = f_{MAX} = 1/t_{RC}$	100 MHz	-	90	mA
			83 MHz	-	80	
			66 MHz	-	70	
			40 MHz	-	60	
$I_{SB1}$	Automatic CE Power-down Current — TTL Inputs	$\text{Max } V_{CC}, \overline{CE} \geq V_{IH}, V_{IN} \geq V_{IH} \text{ or } V_{IN} \leq V_{IL}, f = f_{MAX}$	-	20	mA	
$I_{SB2}$	Automatic CE Power-down Current — CMOS Inputs	$\text{Max } V_{CC}, \overline{CE} \geq V_{CC} - 0.3 \text{ V}, V_{IN} \geq V_{CC} - 0.3 \text{ V}, \text{ or } V_{IN} \leq 0.3 \text{ V}, f = 0$	-	10	mA	

### Notes

2. Tested initially and after any design or process changes that may affect these parameters.
3.  $V_{IL}(\text{min}) = -2.0 \text{ V}$  and  $V_{IH}(\text{max}) = V_{CC} + 2 \text{ V}$  for pulse durations of less than 20 ns.

### Capacitance

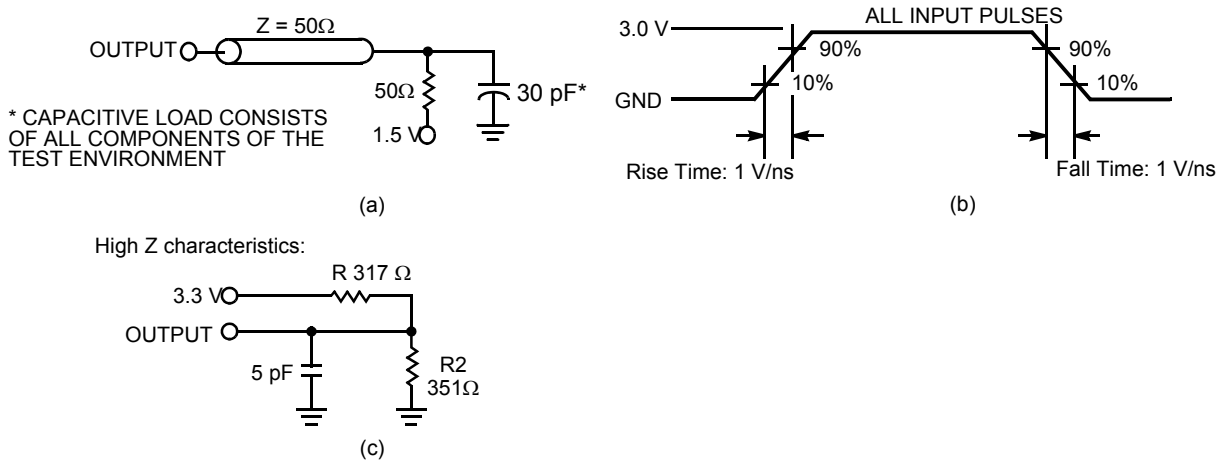
Parameter <sup>[4]</sup>	Description	Test Conditions	Max	Unit
C <sub>IN</sub>	Input capacitance	T <sub>A</sub> = 25 °C, f = 1 MHz, V <sub>CC</sub> = 3.3 V	8	pF
C <sub>OUT</sub>	I/O capacitance		8	pF

### Thermal Resistance

Parameter <sup>[4]</sup>	Description	Test Conditions	TSOP II	VFBGA	Unit
Θ <sub>JA</sub>	Thermal resistance (junction to ambient)	Still air, soldered on a 3 × 4.5 inch, four-layer printed circuit board	50.66	27.89	°C/W
Θ <sub>JC</sub>	Thermal resistance (junction to case)		17.17	14.74	°C/W

### AC Test Loads and Waveforms

Figure 3. AC Test Loads and Waveforms <sup>[5]</sup>



**Note**

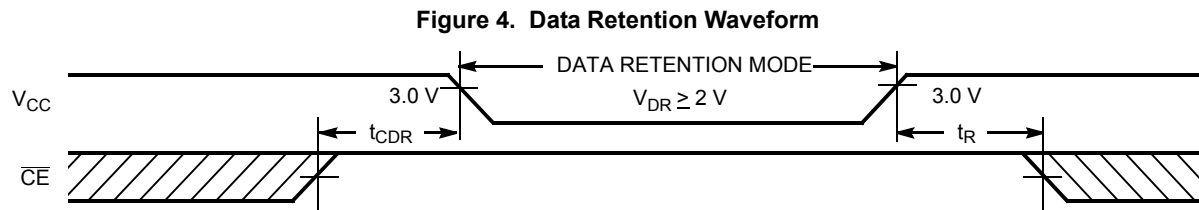
- 4. Tested initially and after any design or process changes that may affect these parameters.
- 5. AC characteristics (except high Z) are tested using the load conditions shown in (a). High Z characteristics are tested for all speeds using the test load shown in (c).

## Data Retention Characteristics

Over the Operating Range

Parameter	Description	Conditions <sup>[6]</sup>	Min	Max	Unit
$V_{DR}$	$V_{CC}$ for data retention		2.0	–	V
$I_{CCDR}$	Data retention current		–	10	mA
$t_{CDR}^{[7]}$	Chip deselect to data retention time	$V_{CC} = V_{DR} = 2.0\text{ V}$ , $\overline{CE} \geq V_{CC} - 0.3\text{ V}$ , $V_{IN} \geq V_{CC} - 0.3\text{ V}$ or $V_{IN} \leq 0.3\text{ V}$	0	–	ns
$t_R^{[8]}$	Operation recovery time		$t_{RC}$	–	ns

## Data Retention Waveform



### Notes

6. No input may exceed  $V_{CC} + 0.3\text{ V}$ .
7. Tested initially and after any design or process changes that may affect these parameters.
8. Full device operation requires linear  $V_{CC}$  ramp from  $V_{DR}$  to  $V_{CC(\text{min.})} \geq 50\ \mu\text{s}$  or stable at  $V_{CC(\text{min.})} \geq 50\ \mu\text{s}$ .

## AC Switching Characteristics

Over the Operating Range

Parameter <sup>[9]</sup>	Description	-10		Unit
		Min	Max	
<b>Read Cycle</b>				
$t_{power}^{[10]}$	$V_{CC}$ (typical) to the first access	100	–	$\mu$ s
$t_{RC}$	Read cycle time	10	–	ns
$t_{AA}$	Address to data valid	–	10	ns
$t_{OHA}$	Data hold from address change	3	–	ns
$t_{ACE}$	$\overline{CE}$ LOW to data valid	–	10	ns
$t_{DOE}$	$\overline{OE}$ LOW to data valid	–	5	ns
$t_{LZOE}$	$\overline{OE}$ LOW to low Z <sup>[11]</sup>	0	–	ns
$t_{HZOE}$	$\overline{OE}$ HIGH to high Z <sup>[11, 12]</sup>	–	5	ns
$t_{LZCE}$	$\overline{CE}$ LOW to low Z <sup>[11]</sup>	3	–	ns
$t_{HZCE}$	$\overline{CE}$ HIGH to high Z <sup>[11, 12]</sup>	–	5	ns
$t_{PU}$	$\overline{CE}$ LOW to power-up	0	–	ns
$t_{PD}$	$\overline{CE}$ HIGH to power-down	–	10	ns
$t_{DBE}$	Byte enable to data valid	–	5	ns
$t_{LZBE}$	Byte enable to low Z	0	–	ns
$t_{HZBE}$	Byte disable to high Z	–	6	ns
<b>Write Cycle <sup>[13, 14]</sup></b>				
$t_{WC}$	Write cycle time	10	–	ns
$t_{SCE}$	$\overline{CE}$ LOW to write end	7	–	ns
$t_{AW}$	Address set-up to write end	7	–	ns
$t_{HA}$	Address hold from write end	0	–	ns
$t_{SA}$	Address set-up to write start	0	–	ns
$t_{PWE}$	$\overline{WE}$ pulse width	7	–	ns
$t_{SD}$	Data set-up to write end	5	–	ns
$t_{HD}$	Data hold from write end	0	–	ns
$t_{LZWE}$	$\overline{WE}$ HIGH to low Z <sup>[11]</sup>	3	–	ns
$t_{HZWE}$	$\overline{WE}$ LOW to high Z <sup>[11, 12]</sup>	–	5	ns
$t_{BW}$	Byte enable to end of write	7	–	ns

### Notes

9. Test conditions assume signal transition time of 3 ns or less, timing reference levels of 1.5 V, input pulse levels of 0 to 3.0 V.
10.  $t_{POWER}$  gives the minimum amount of time that the power supply should be at typical  $V_{CC}$  values until the first memory access is performed.
11. At any given temperature and voltage condition,  $t_{HZCE}$  is less than  $t_{LZCE}$ ,  $t_{HZOE}$  is less than  $t_{LZOE}$ ,  $t_{HZBE}$  is less than  $t_{LZBE}$ , and  $t_{HZWE}$  is less than  $t_{LZWE}$  for any given device.
12.  $t_{HZOE}$ ,  $t_{HZCE}$ ,  $t_{HZBE}$  and  $t_{HZWE}$  are specified with a load capacitance of 5 pF as in part (d) of AC Test Loads. Transition is measured when the outputs enter a high impedance state.
13. The internal write time of the memory is defined by the overlap of  $\overline{CE}$  LOW, and  $\overline{WE}$  LOW.  $\overline{CE}$  and  $\overline{WE}$  must be LOW to initiate a write, and the transition of either of these signals can terminate the write. The input data set-up and hold timing should be referenced to the leading edge of the signal that terminates the write.
14. The minimum write cycle pulse width for Write Cycle No. 4 ( $\overline{WE}$  Controlled,  $\overline{OE}$  LOW) should be the sum of  $t_{SD}$  and  $t_{HZWE}$ .

Switching Waveforms

Figure 5. Read Cycle No. 1 [15, 16]

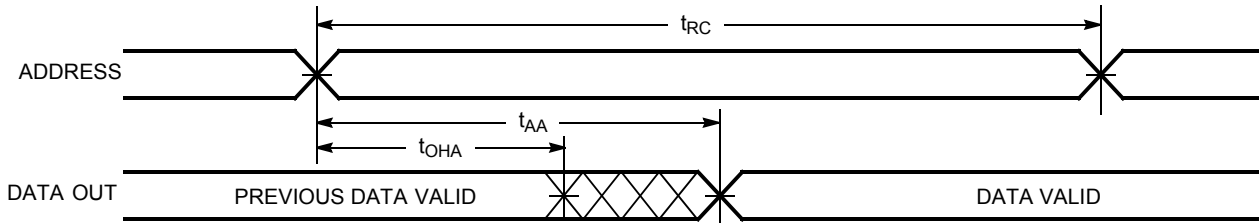
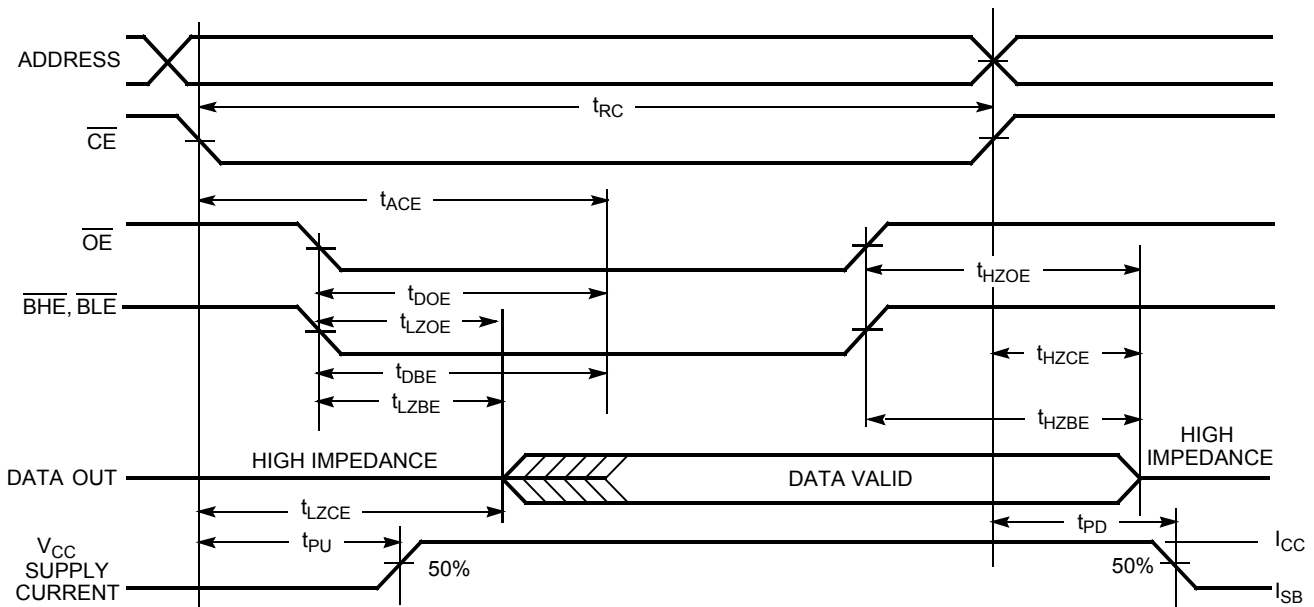


Figure 6. Read Cycle No. 2 ( $\overline{OE}$  Controlled) [16, 17]



Notes

- 15. Device is continuously selected.  $\overline{OE}$ ,  $\overline{CE}$ ,  $\overline{BHE}$  and/or  $\overline{BLE}$  =  $V_{IL}$ .
- 16.  $\overline{WE}$  is HIGH for read cycle.
- 17. Address valid prior to or coincident with  $\overline{CE}$  transition LOW.



Switching Waveforms (continued)

Figure 7. Write Cycle No. 1 ( $\overline{\text{CE}}$  Controlled) [18, 19]

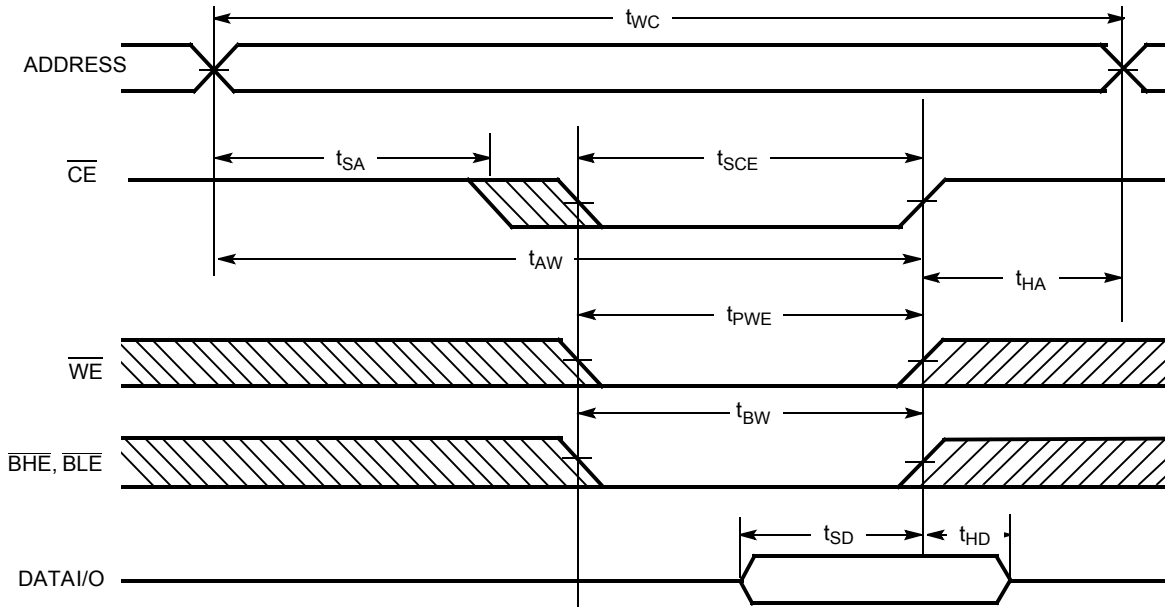
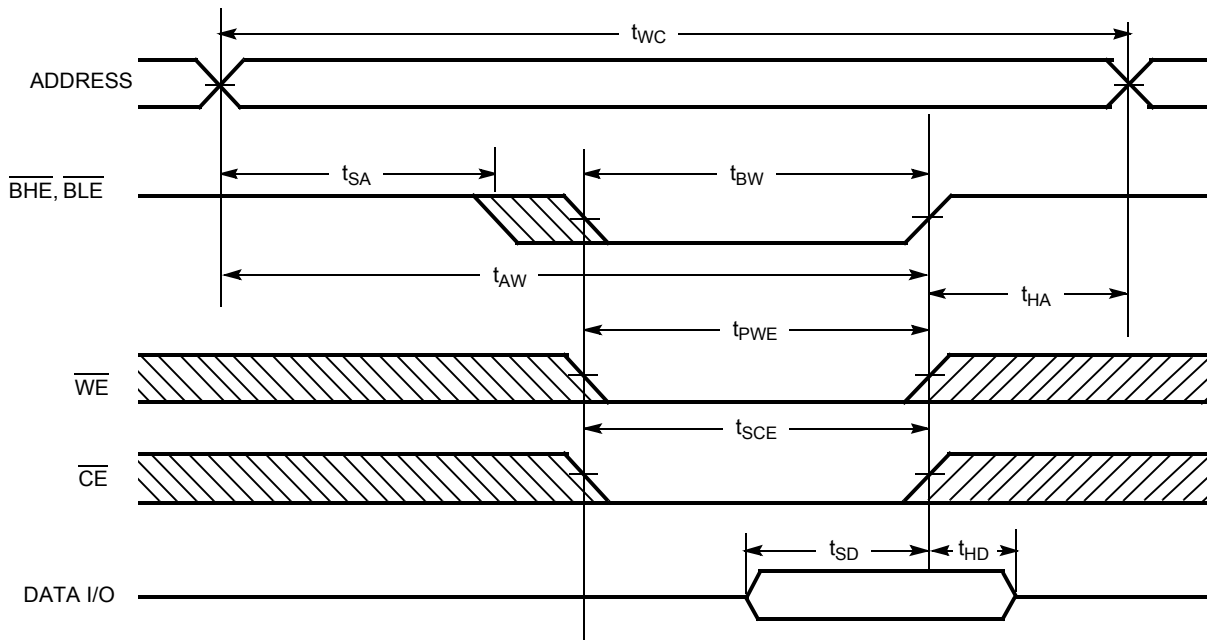


Figure 8. Write Cycle No. 2 ( $\overline{\text{BLE}}$  or  $\overline{\text{BHE}}$  Controlled)



Notes

- 18. Data I/O is high-impedance if  $\overline{\text{OE}}$  or  $\overline{\text{BHE}}$  and/or  $\overline{\text{BLE}} = V_{IH}$ .
- 19. If  $\overline{\text{CE}}$  goes HIGH simultaneously with  $\overline{\text{WE}}$  going HIGH, the output remains in a high-impedance state.

Switching Waveforms (continued)

Figure 9. Write Cycle No. 3 ( $\overline{WE}$  Controlled,  $\overline{OE}$  HIGH During Write) [20, 21]

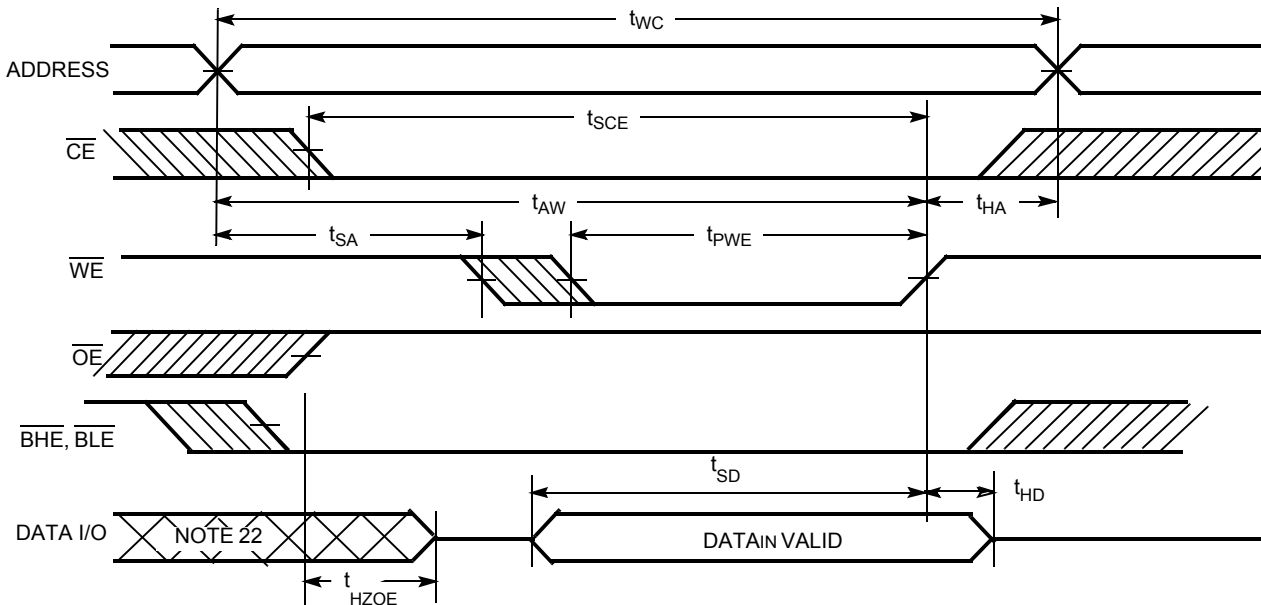
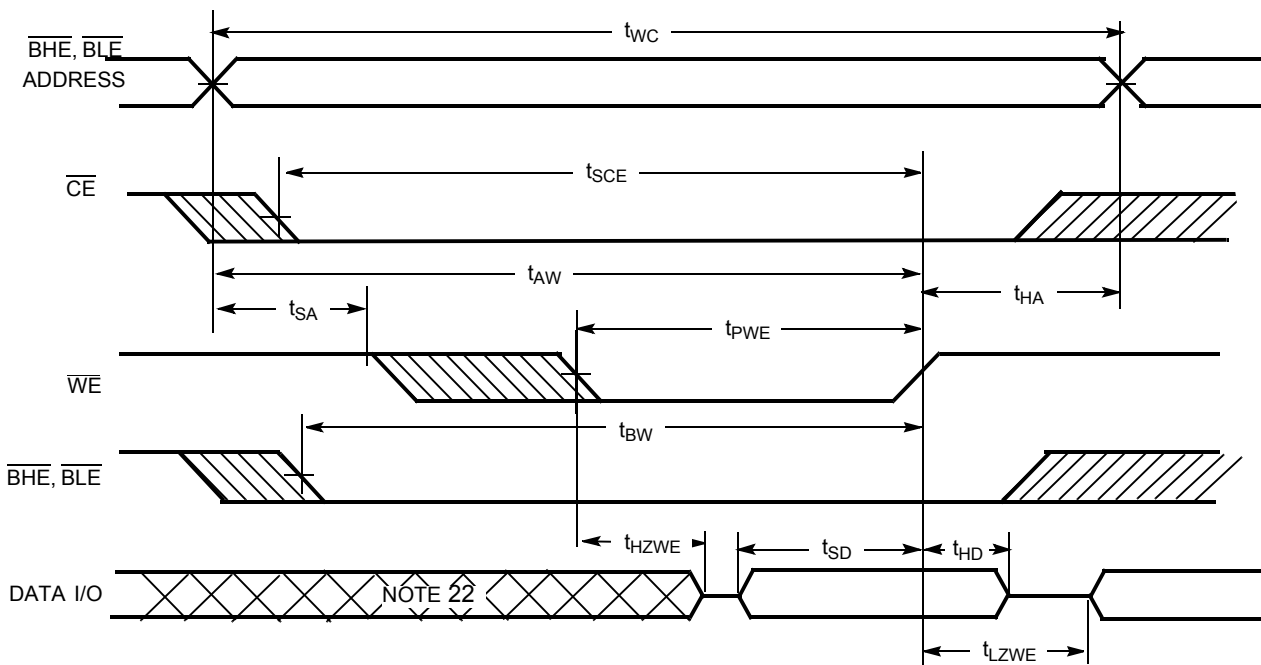


Figure 10. Write Cycle No. 4 ( $\overline{WE}$  Controlled,  $\overline{OE}$  LOW) [23]



Notes

- 20. Data I/O is high-impedance if  $\overline{OE}$  or  $\overline{BHE}$  and/or  $\overline{BLE} = V_{IH}$ .
- 21. If  $\overline{CE}$  goes HIGH simultaneously with  $\overline{WE}$  going HIGH, the output remains in a high-impedance state.
- 22. During this period the I/Os are in the output state and input signals should not be applied.
- 23. The minimum write pulse width for Write Cycle No. 4 ( $\overline{WE}$  controlled,  $\overline{OE}$  LOW) should be the sum of  $t_{SD}$  and  $t_{HZWE}$ .

**Truth Table**

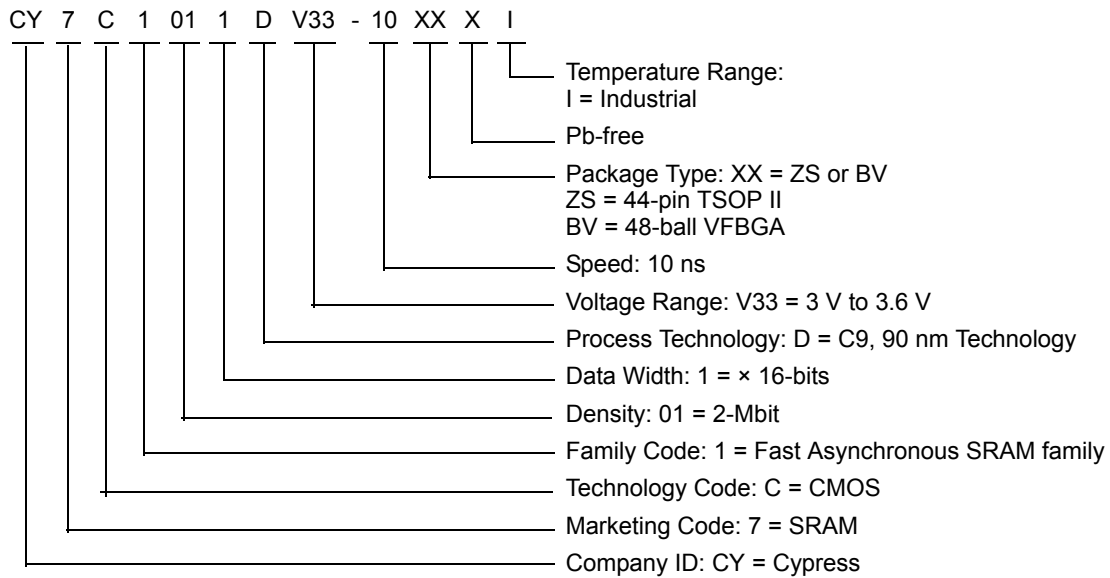
$\overline{CE}$	$\overline{OE}$	$\overline{WE}$	$\overline{BLE}$	$\overline{BHE}$	I/O <sub>0</sub> –I/O <sub>7</sub>	I/O <sub>8</sub> –I/O <sub>15</sub>	Mode	Power
H	X	X	X	X	High Z	High Z	Power-down	Standby (I <sub>SB</sub> )
L	L	H	L	L	Data Out	Data Out	Read all bits	Active (I <sub>CC</sub> )
L	L	H	L	H	Data Out	High Z	Read lower bits only	Active (I <sub>CC</sub> )
L	L	H	H	L	High Z	Data Out	Read upper bits only	Active (I <sub>CC</sub> )
L	X	L	L	L	Data In	Data In	Write all bits	Active (I <sub>CC</sub> )
L	X	L	L	H	Data In	High Z	Write lower bits only	Active (I <sub>CC</sub> )
L	X	L	H	L	High Z	Data In	Write upper bits only	Active (I <sub>CC</sub> )
L	H	H	X	X	High Z	High Z	Selected, outputs disabled	Active (I <sub>CC</sub> )

**Ordering Information**

Speed (ns)	Ordering Code	Package Diagram	Package Type	Operating Range
10	CY7C1011DV33-10ZSXI	51-85087	44-pin TSOP II (Pb-free)	Industrial
	CY7C1011DV33-10BVXI	51-85150	48-ball VFBGA (Pb-free)	

Please contact your local Cypress sales representative for availability of these parts

**Ordering Code Definitions**



Package Diagrams

Figure 11. 44-pin TSOP Z44-II Package Outline, 51-85087

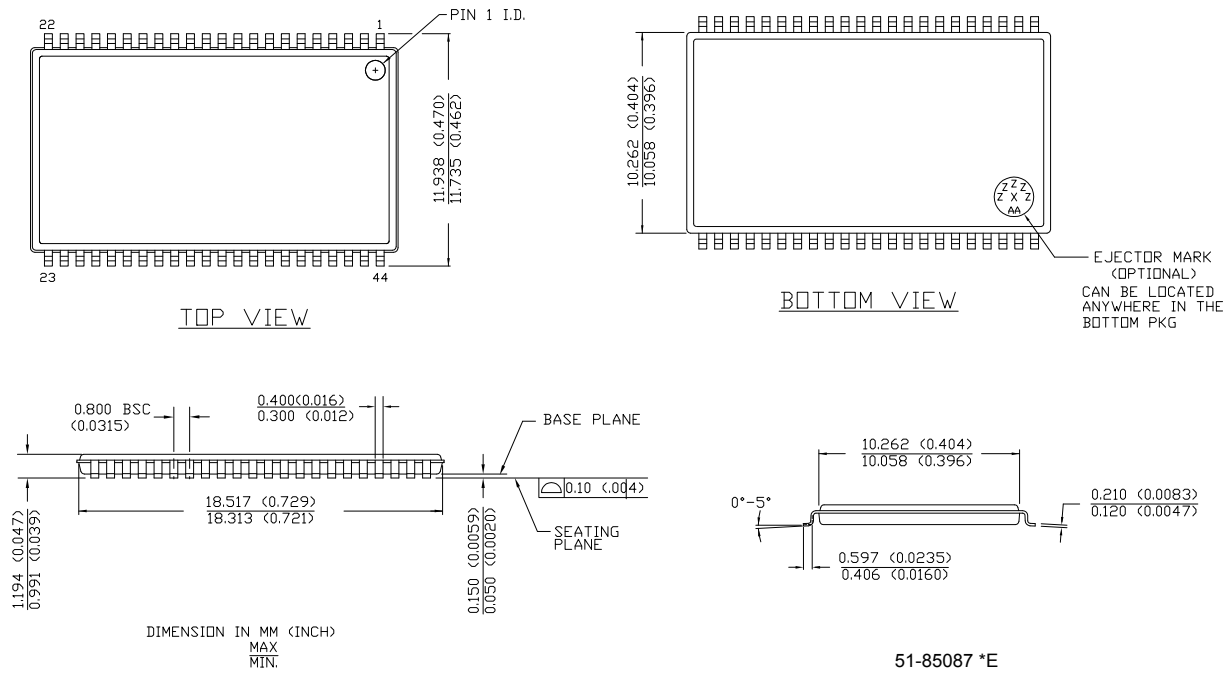
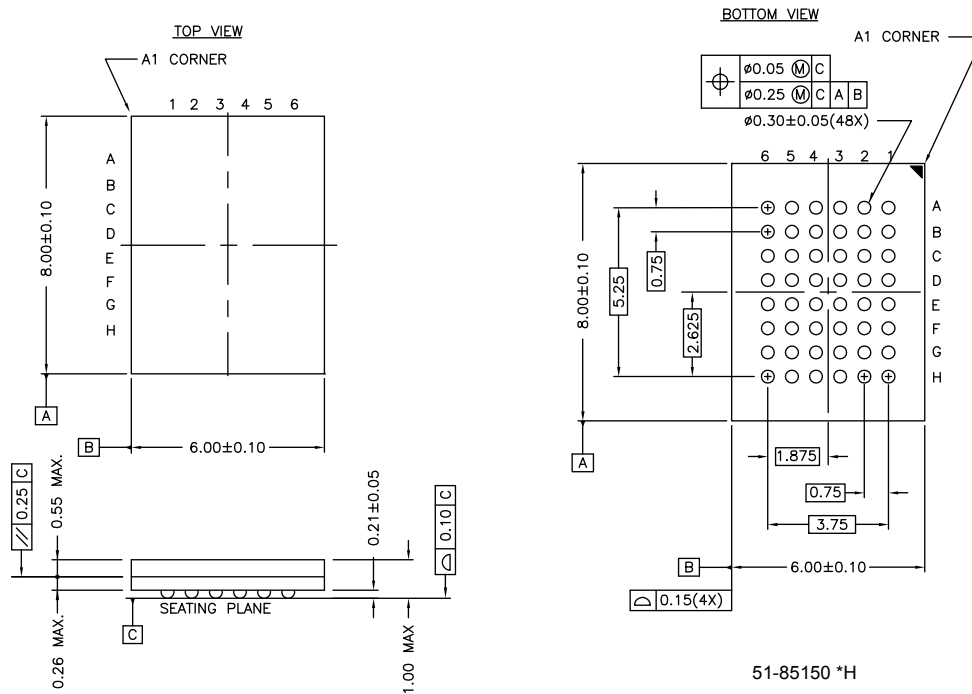


Figure 12. 48-ball VFBGA (6 × 8 × 1 mm) BV48/BZ48 Package Outline, 51-85150



## Acronyms

Acronym	Description
CMOS	Complementary Metal Oxide Semiconductor
$\overline{CE}$	Chip Enable
I/O	Input/Output
$\overline{OE}$	Output Enable
SRAM	Static Random Access Memory
TSOP	Thin Small Outline Package
TTL	Transistor-Transistor Logic
VFBGA	Very Fine-Pitch Ball Grid Array
$\overline{WE}$	Write Enable

## Document Conventions

### Units of Measure

Symbol	Unit of Measure
°C	degree Celsius
MHz	megahertz
μs	microsecond
μA	microampere
mA	milliampere
ns	nanosecond
%	percent
pF	picofarad
V	volt
W	watt

**Document History**

Document Title: CY7C1011DV33, 2-Mbit (128 K × 16) Static RAM				
Document Number: 38-05609				
Rev.	ECN No.	Issue Date	Orig. of Change	Description of Change
**	250650	See ECN	RKF	New data sheet.
*A	399070	See ECN	NXR	<p>Changed from Advance to Preliminary</p> <p>Changed address of Cypress Semiconductor Corporation on Page# 1 from "3901 North First Street" to "198 Champion Court"</p> <p>Removed TQFP Package from product offering</p> <p>Removed –15 speed bin</p> <p>Corrected DC voltage limits in maximum ratings section from –0.5 to –0.3V and <math>V_{CC} +0.5V</math> to <math>V_{CC} +0.3V</math></p> <p>Redefined <math>I_{CC}</math> values for Com'l and Ind'l temperature ranges</p> <p><math>I_{CC}</math> (Com'l): Changed from 100, 80 and 70 mA to 90, 80 and 75 mA for 8, 10 and 12ns speed bins respectively</p> <p><math>I_{CC}</math> (Ind'l): Changed from 80 and 70 mA to 90 and 85 mA for 10 and 12ns speed bins respectively</p> <p>Modified Note# 4 on AC Test Loads</p> <p>Added Static Discharge Voltage and latch-up current spec</p> <p>Added <math>V_{IH(max)}</math> spec in Note# 2</p> <p>Changed reference voltage level for measurement of Hi-Z parameters from <math>\pm 500</math> mV to <math>\pm 200</math> mV</p> <p>Added Data Retention Characteristics Table and footnote on <math>t_R</math></p> <p>Added Write Cycle (WE Controlled, OE HIGH During Write) Timing Diagram</p> <p>Changed package name for 44-pin TSOP II from Z to ZS</p> <p>Added 8 ns parts in the Ordering Information table</p> <p>Shaded Ordering Information Table</p>
*B	459073	See ECN	NXR	<p>Converted Preliminary to Final.</p> <p>Removed –8 and –12 Speed bins</p> <p>Removed Commercial Operating Range from product offering.</p> <p>Changed the description of <math>I_{IX}</math> from "Input Load Current" to "Input Leakage Current"</p> <p>Updated the Thermal Resistance table.</p> <p>Changed <math>t_{HZBE}</math> from 5 ns to 6 ns.</p> <p>Updated footnote #7 on High-Z parameter measurement</p> <p>Added footnote #12.</p> <p>Updated the Ordering Information and replaced Package Name column with Package Diagram in the Ordering Information table.</p>
*C	480177	See ECN	VKN	Added -10BVI product ordering code in the Ordering Information table.
*D	3059162	10/14/2010	PRAS	<p>Added <a href="#">Ordering Code Definitions</a>.</p> <p>Updated <a href="#">Package Diagrams</a>.</p>
*E	3098812	12/01/2010	PRAS	<p>Added <a href="#">Acronyms and Units of Measure</a>.</p> <p>Minor edits and updated in new template.</p>
*F	3861347	01/08/2013	TAVA	<p>Updated <a href="#">Ordering Information</a> (Updated part numbers).</p> <p>Updated <a href="#">Package Diagrams</a>:</p> <p>spec 51-85087 – Changed revision from *C to *E.</p> <p>spec 51-85150 – Changed revision from *F to *H.</p>
*G	4187715	11/10/2013	MEMJ	<p>Updated in new template.</p> <p>Completing Sunset Review.</p>

**Document History** *(continued)*

Document Title: CY7C1011DV33, 2-Mbit (128 K × 16) Static RAM				
Document Number: 38-05609				
Rev.	ECN No.	Issue Date	Orig. of Change	Description of Change
*H	4567909	11/12/2014	MEMJ	<p>Updated <a href="#">Functional Description</a>: Added "For a complete list of related resources, <a href="#">click here.</a>" at the end.</p> <p>Updated <a href="#">Switching Waveforms</a>: Added Note 23 and referred the same note in <a href="#">Figure 10</a>.</p> <p>Competing Sunset Review.</p>



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